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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

Complete if Known

Application Number 09/328,939
Filing Date June 9, 1999
First Named Inventor Fujimim, Shuzo
Group Art Unit 1746
Examiner Name Shamim Ahmed
Attorney Docket Number 018867-000410US

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
SA	A	5,403,436		Fujimura et al.	05/04/1995	
SA	B	6,149,829		Takamatsu, et al.	11/21/2000	

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
SA	C	Japan	75229	H7	KOKAI			yes

Examiner Signature

Shamim Ahmed

Date Considered

6/25/02

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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 2

Complete if Known

Application Number	09/328,939
Filing Date	June 9, 1999
First Named Inventor	Fujimim, Shuzo
Group Art Unit	1746
Examiner Name	Shamim Ahmed
Attorney Docket Number	018867-000410US

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SA	D	FUJIMURA et al., "Study on Ashing Process for Removal of ion Implanted Resist Layer", Process Symposium, Dry Process, Procedure Vol. 88-7, Honolulu, Hawaii, May 1987 (The Electro Chemical Society Inc. Pennington, 1988), pp. 126-133	<input type="checkbox"/>
SA	E	FUJIMURA et al., "Resist Stripping in an O ₂ +H ₂ O Plasma Downstream", J. Vac. Sci. Technol. B9 (2), Mar/Apr 1991, pp. 357-361	<input type="checkbox"/>
SA	F	KIKUCHI et al., "Effects of H ₂ O on Atomic Hydrogen Generation in Hydrogen Plasma", Jpn. J. Appl. Phys., Vol. 32 (1993), Part 1, No. 6B, June 1993, pp. 3120-3124	<input type="checkbox"/>
SA	G	KIKUCHI et al., "Cleaning of Silicon Surfaces by NF ₃ - Added Hydrogen and Water-Vapor Plasma Downstream Treatment", Jpn. J. Appl. Phys., Vol. 35 (1996), Part 1, No. 2B, February 1996, pp. 1022-1026	<input type="checkbox"/>
SA	H	KIM et al., "Recombination of O, N, and H Atoms on Silica: Kinetics and Mechanism", Langmuir 1991, Vol. 7, No. 12, pp.2999-3005	<input type="checkbox"/>
SA	I	MARTIN, "Diamond Film Growth in a Flowtube: A Temperature Dependence Study", J. Appl. Phys., Vol. 70., No. 10, November 15, 1991, pp. 5667-5674	<input type="checkbox"/>
SA	J	Papers by S. FUJIMURA, H. YANO, J. KONNO, T. TAKADA. AND K. INAYOSHI: Study on aching process for removal ion implanted resist layer, Process Symposium, Dry Process, Procedure Vol. 88-7, Honolulu, Hawaii May 1987 (The electro chemical Society Inc. Penninton, 1988) pp. 126-133	<input type="checkbox"/>
SA	K	J. KIKUCHI, M. IGA, H. OGAWA, S. FUJIMURA, AND H. YANO: Native oxide removal on Si surface by NF ₃ -added hydrogen and water vapor plasma downstream treatment, Jpn. J. Appl. Phys, 35, 1022-1026 (1996)	<input type="checkbox"/>
SA	L	J. VAC Sci Tehnol B, 9, 357-361 (1991)	<input type="checkbox"/>
SA	M	L. BROWN, J.Phys. Chem., 71, 2429 (1967).	<input type="checkbox"/>
SA	N	LEE et al., "Chrome and Zinc Contaminants Removal from Silicon (100) Surfaces," Jpn. J. Appl. Phys., 40:4002-4006 (2001). June	<input type="checkbox"/>
SA	O	"YOUNG C. KIM AND MICHAEL BOUDANT, recombination of O, N, and H atoms as Silica:Kinetics and mechanism, hagemuir, 7, 2999-3005 (1991), and L. Robbin Martin, "Diamond film growth in a flowtube : A temperature dependance study; J. Appl. Phys., 70, 5667-5674 (1991)".	<input type="checkbox"/>

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